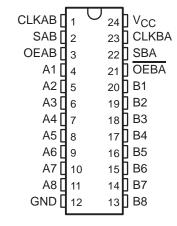
- State-of-the-Art EPIC-IIB™ BiCMOS Design Significantly Reduces Power Dissipation
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- Typical V<sub>OLP</sub> (Output Ground Bounce) < 1 V at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C
- High-Drive Outputs (-32-mA I<sub>OH</sub>, 64-mA I<sub>OL</sub>)
- Multiplexed Real-Time and Stored Data
- Inverting Data Paths
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Plastic (NT) and Ceramic (JT) DIPs

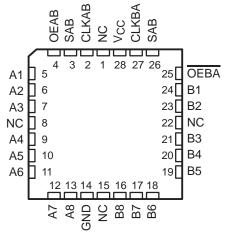
#### description

These devices consist of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. Output-enable (OEAB and OEBA) inputs are provided to control the transceiver functions. The select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'ABT651 devices.

SN54ABT651 . . . JT PACKAGE SN74ABT651 . . . DB, DW, NT, OR PW PACKAGE (TOP VIEW)



SN54ABT651 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it also is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and OEBA. In this configuration, each output reinforces its input. When all the other data sources to the two sets of bus lines are at high impedance, each set remains at its last state.

To ensure the high-impedance state during power up or power down,  $\overline{\text{OEBA}}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver (B to A). OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver (A to B).



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SCBS083E - JANUARY 1991 - REVISED APRIL 1998

#### description (continued)

The SN54ABT651 is characterized for operation over the full military temperature range of  $-55^{\circ}$ C to  $125^{\circ}$ C. The SN74ABT651 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C.

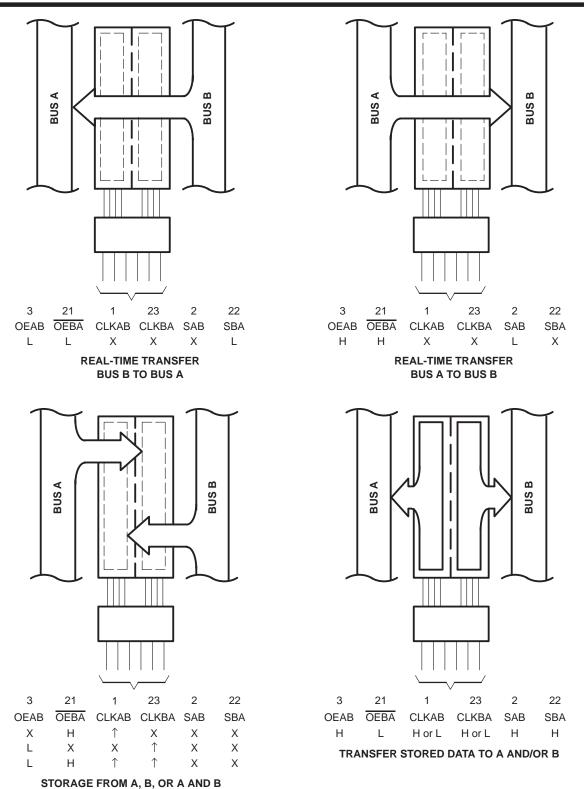
#### **FUNCTION TABLE**

		INPU <sup>-</sup>	rs			DAT	A I/O	OPERATION OR FUNCTION
OEAB	OEBA	CLKAB	CLKBA	SAB	SBA	A1-A8	B1-B8	OPERATION OR FUNCTION
L	Н	H or L	H or L	Х	Х	Input	Input	Isolation
L	Н	1	1	X	X	Input	Input	Store A and B data
Х	Н	1	H or L	Х	Х	Input	Unspecified <sup>†</sup>	Store A, hold B
Н	Н	$\uparrow$	1	X‡	X	Input	Output	Store A in both registers
L	Х	H or L	1	Х	Х	Unspecified <sup>†</sup>	Input	Hold A, store B
L	L	1	1	Χ	X‡	Output	Input	Store B in both registers
L	L	Х	Χ	Х	L	Output	Input	Real-time B data to A bus
L	L	Χ	H or L	X	Н	Output	Input	Stored $\overline{B}$ data to A bus
Н	Н	Χ	Χ	L	Х	Input	Output	Real-time A data to B bus
Н	Н	H or L	Χ	Н	X	Input	Output	Stored $\overline{A}$ data to B bus
Н	L	H or L	H or L	Н	Н	Output	Output	Stored A data to B bus and stored B data to A bus

<sup>†</sup> The data output functions may be enabled or disabled by a variety of level combinations at OEAB or OEBA. Data input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



<sup>‡</sup> When select control is low, clocks can occur simultaneously if allowances are made for propagation delays from A to B (B to A) plus setup and hold times. When select control is high, clocks must be staggered to load both registers.



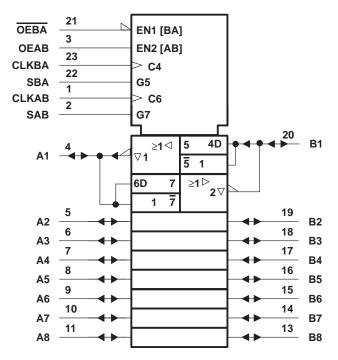
Pin numbers are for the DB, DW, JT, NT, and PW packages.

Figure 1. Bus-Management Functions



SCBS083E - JANUARY 1991 - REVISED APRIL 1998

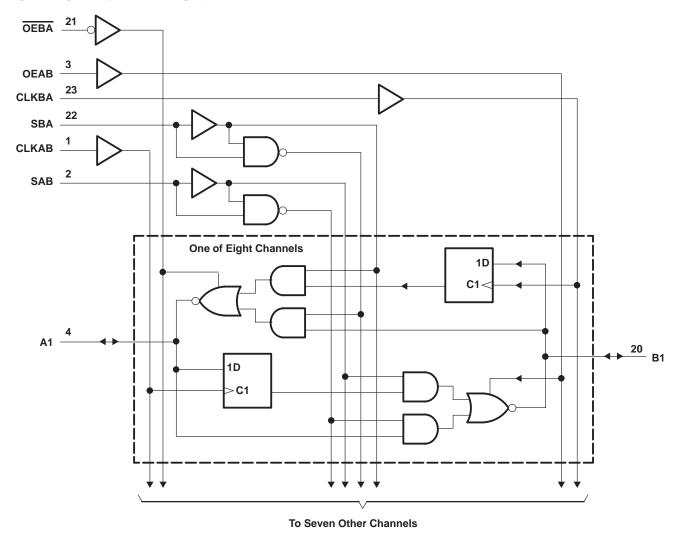
## logic symbol†



<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the DB, DW, JT, NT, and PW packages.



## logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, NT, and PW packages.

SCBS083E - JANUARY 1991 - REVISED APRIL 1998

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>		0.5 V to 7 V
Input voltage range, V <sub>I</sub> (except I/O ports) (see N		
Voltage range applied to any output in the high	or power-off state, VO	
Current into any output in the low state, IO: SN	54ABT651	96 mA
SN <sup>-</sup>	74ABT651	128 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)		–18 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)		–50 mA
Package thermal impedance, $\theta_{JA}$ (see Note 2):	DB package	104°C/W
***	DW package	81°C/W
	NT package	67°C/W
	PW package	120°C/W
Storage temperature range, T <sub>stg</sub>		–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

### recommended operating conditions (see Note 3)

		SN54A	BT651	SN74A	BT651	UNIT
		MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2	EN	2		V
VIL	Low-level input voltage		0.8		0.8	V
٧ı	Input voltage	0 <	Vcc	0	VCC	V
IOH	High-level output current	(ر)	-24		-32	mA
lOL	Low-level output current	$g_{Q_{\ell}}$	48		64	mA
Δt/Δν	Input transition rise or fall rate	) V	5		5	ns/V
TA	Operating free-air temperature	<b>–</b> 55	125	-40	85	°C

NOTE 3: All unused pins (control or I/O) of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

<sup>2.</sup> The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CON	IDITIONS	Т	A = 25°C	;	SN54A	BT651	SN74A	BT651	UNIT
PARAMETER	TEST CON	ADITIONS	MIN	TYP†	MAX	MIN	MAX	MIN	MAX	UNII
VIK	V <sub>CC</sub> = 4.5 V,	I <sub>I</sub> = -18 mA			-1.2		-1.2		-1.2	V
	$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -3 \text{ mA}$	2.5			2.5		2.5		
Va	$V_{CC} = 5 V$ ,	$I_{OH} = -3 \text{ mA}$	3			3		3		V
VOH	V <sub>CC</sub> = 4.5 V	$I_{OH} = -24 \text{ mA}$	2			2				v
	VCC = 4.5 V	$I_{OH} = -32 \text{ mA}$	2*					2		
VOL	V <sub>CC</sub> = 4.5 V	I <sub>OL</sub> = 48 mA			0.55		0.55			V
VOL	VCC = 4.5 V	$I_{OL} = 64 \text{ mA}$			0.55*				0.55	V
V <sub>hys</sub>				100			4			mV
Control inputs	V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = V <sub>CC</sub> or GND			±1		<u></u> ±1		±1	μΑ
A or B ports	VCC = 3.5 V,	1 = 100 01 014D			±100		±100		±100	μΑ
lozh <sup>‡</sup>	$V_{CC} = 5.5 \text{ V},$	$V_0 = 2.7 \text{ V}$			50		50		50	μΑ
l <sub>OZL</sub> ‡	V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 0.5 V			-50	S	-50		-50	μΑ
l <sub>off</sub>	$V_{CC} = 0$ ,	$V_I$ or $V_O \le 4.5 \text{ V}$			±100	0			±100	μΑ
ICEX	V <sub>CC</sub> = 5.5 V, V <sub>O</sub> = 5.5 V	Outputs high			50	40	50		50	μА
IO§	V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 2.5 V	-50	-100	-180	-50	-180	-50	-180	mA
	V <sub>CC</sub> = 5.5 V,	Outputs high			250		250		250	μΑ
Icc	$I_{O} = 0$ ,	Outputs low			30		30		30	mA
	$V_I = V_{CC}$ or GND	Outputs disabled			250		250		250	μΑ
ΔICC¶	$V_{CC} = 5.5 \text{ V}$ , One input Other inputs at $V_{CC}$				1.5		1.5		1.5	mA
C <sub>i</sub> Control inputs	V <sub>I</sub> = 2.5 V or 0.5 V			6						pF
C <sub>io</sub> A or B ports	V <sub>O</sub> = 2.5 V or 0.5 V			7.5						pF

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter does not apply.

## timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 2)

		V <sub>CC</sub> :	V <sub>CC</sub> = 5 V, T <sub>A</sub> = 25°C		BT651	SN74AI	BT651	UNIT
		MIN MAX		MIN	MAX	MIN	MAX	
fclock	Clock frequency		125		125		125	MHz
t <sub>W</sub>	Pulse duration, CLK high or low	4		4	10,71	4		ns
t <sub>su</sub>	Setup time, A or B before CLKAB↑ or CLKBA↑	3		3	71.	3		ns
t <sub>h</sub>	Hold time, A or B after CLKAB↑ or CLKBA↑	0		0		0		ns

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ .

<sup>&</sup>lt;sup>‡</sup> The parameters I<sub>OZH</sub> and I<sub>OZL</sub> include the input leakage current.

<sup>§</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

 $<sup>\</sup>P$  This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

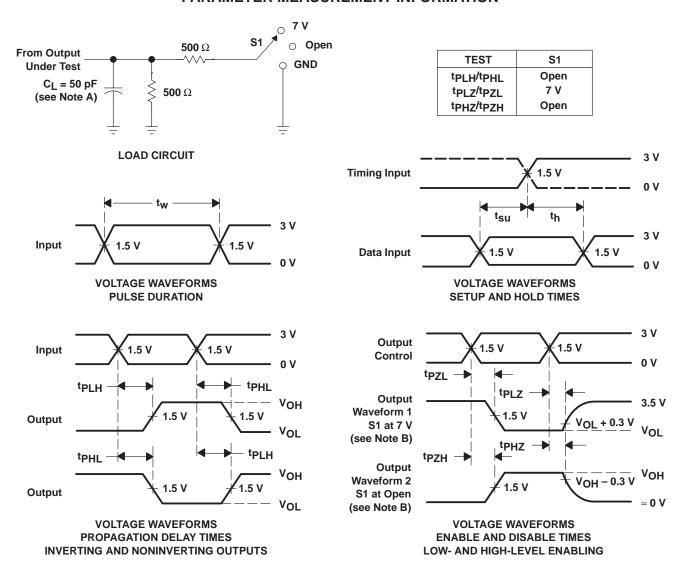
SCBS083E - JANUARY 1991 - REVISED APRIL 1998

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L$ = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V(	CC = 5 V 4 = 25°C	/, }	SN54A	BT651	SN74A	BT651	UNIT
	(INFOT)	(001F01)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f <sub>max</sub>			125			125		125		MHz
<sup>t</sup> PLH	CLKBA or CLKAB	A or B	2.2	4	5.1	2.2	5.9	2.2	5.6	ns
<sup>t</sup> PHL	CERBA OF CERAB	Aorb	1.7	4	5.1	1.7	5.9	1.7	5.6	115
<sup>t</sup> PLH	A or B	B or A	1.5	4	5.1	1.5	6.4	1.5	6.2	ns
<sup>t</sup> PHL	AUIB	BULK	1.5	3.3	4.6	1.5	5.6	1.5	5.4	115
t <sub>PLH</sub>	SAB or SBA†	A or B	1.5	4	5.1	1.5	6.8	1.5	6.5	ns
t <sub>PHL</sub>		AOID	1.5	3.6	4.9	1.5	6.2	1.5	5.9	113
<sup>t</sup> PZH	<del>OEBA</del>	А	1.3	3.6	4.6	1.3	5.9	1.3	5.8	ns
t <sub>PZL</sub>	OEBA	A	2.5	5.7	6.8	2.5	8.9	2.5	8.5	115
<sup>t</sup> PHZ	<del>OEBA</del>	А	1.5	3.2	4.5	91.5	6.2	1.5	5	ns
<sup>t</sup> PLZ	OEBA	٨	1.5	3	3.8	1.5	4.3	1.5	4.1	115
<sup>t</sup> PZH	OEAB	В	1.8	4.3	6.1	1.8	6.7	1.8	6.5	ns
tPZL	OLAB	ט	2.9	5.5	6.5	2.9	7.6	2.9	7.4	115
<sup>t</sup> PHZ	OEAB	В	1.5	3.3	4.5	1.5	6.5	1.5	5.5	ns
<sup>t</sup> PLZ	OLAB	ь	1.5	3.4	4.4	1.5	5.2	1.5	5.1	110

<sup>†</sup> These parameters are measured with the internal output state of the storage register opposite that of the bus input.

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74ABT651DW	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651
SN74ABT651DW.B	Active	Production	SOIC (DW)   24	25   TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651
SN74ABT651DWR	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651
SN74ABT651DWR.B	Active	Production	SOIC (DW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT651

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

## **PACKAGE MATERIALS INFORMATION**

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#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ABT651DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

## **PACKAGE MATERIALS INFORMATION**

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#### \*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
I	SN74ABT651DWR	SOIC	DW	24	2000	350.0	350.0	43.0

## **PACKAGE MATERIALS INFORMATION**

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#### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74ABT651DW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74ABT651DW.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

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